



PNP Silicon Small Signal Transistor

Qualified per MIL-PRF-19500/382

Qualified Levels: JAN, JANTX, and **JANTXV**

DESCRIPTION

This 2N2944A through 2N2946A PNP silicon transistor device is military qualified up to a JANTXV level for high-reliability applications. Microsemi also offers numerous other products to meet higher and lower power voltage regulation applications.

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- JEDEC registered 2N2944A thru 2N2946A series.
- JAN, JANTX, and JANTXV qualifications per MIL-PRF-19500/382 available.
- RoHS compliant versions available (commercial grade only).

TO-46 (TO-206AB) **Package**

Also available in:

📜 UB package (surface mount) 2N2944AUB - 2N2946AUB

APPLICATIONS / BENEFITS

- Low profile metal can package.
- ESD to Class 3 per MIL-STD-750, method 1020.

MAXIMUM RATINGS @ +25 °C unless specified otherwise.

Parameters/Test Conditions		Symbol	Value	Unit
Junction and Storage Temperature		T_J and T_{STG}	-65 to +200	°C
Thermal Resistance Junction-to-Ambier	nt	R _{OJA}	435	°C/W
Collector Current (dc)		I _C	-100	mA
Emitter to Base voltage (static),	2N2944A	V_{EBO}	-15	V
collector open	2N2945A		-25	
	2N2946A		-40	
Collector to Base voltage (static),	2N2944A	V_{CBO}	-15	V
emitter open	2N2945A		-25	
	2N2946A		-40	
Collector to Emitter voltage (static),	2N2944A	V_{CEO}	-10	V
base open	2N2945A		-20	
	2N2946A		-35	
Emitter to Collector voltage	2N2944A	V_{ECO}	-10	V
	2N2945A		-20	
	2N2946A		-35	
Total Power Dissipation, all terminals @	P_{T}	400	mW	

Notes: 1. Derate linearly 2.30 mW /°C above T_A = +25 °C.

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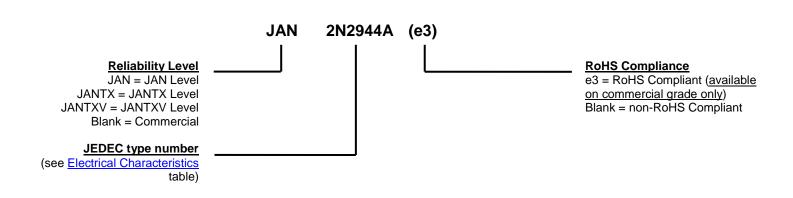
www.microsemi.com



MECHANICAL and PACKAGING

- CASE: Nickel plated kovar, glass seals.
- TERMINALS: Gold plating over nickel, solder dipped, kovar.
- MARKING: Part number, date code, manufacturer's ID.
- WEIGHT: 0.234 grams.
- See Package Dimensions on last page.

PART NOMENCLATURE



	SYMBOLS & DEFINITIONS				
Symbol	Definition				
I _B	Base current (dc).				
Ι _Ε	Emitter current (dc).				
V_{CB}	Collector to base voltage (dc).				
V_{EB}	Emitter to base voltage (dc).				
$V_{(BR)}$	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.				



ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise noted.

Characteristic		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS:		<u>, , , , , , , , , , , , , , , , , , , </u>		<u>I</u>	
Collector-Emitter Breakdown Voltage					
$I_{C} = -10 \mu A$	2N2944A	V(BR)CEO	-10		V
	2N2945A	(=13)0=0	-20		
	2N2946A		-35		
Emitter-Collector Breakdown Voltage					
$I_E = -10 \mu A, I_B = 0$	2N2944A	V(BR)ECO	-10		V
	2N2945A	(BIT)LOO	-20		
	2N2946A		-35		
Collector-Base Cutoff Current					
Vcb = -15 V	2N2944A	ICBO	10		μΑ
Vcb = -25 V	2N2945A	ЮВО	10		μιτ
Vcb = -40 V	2N2946A		10		
Emitter-Base Cutoff Current	211204071				
VEB = -12 V	2N2944A	IEBO		-0.1	ηΑ
VEB = -12 V VEB = -20 V	2N2944A 2N2945A	·LBO		-0.2	17.
VEB = -32 V VEB = -32 V	2N2946A			-0.5	
ON CHARACTERISTICS: (1)	21125-1071			0.0	
Forward-Current Transfer Ratio					
$I_C = -1.0 \text{ mA}, V_{CE} = -0.5 \text{ V}$	2N2944A	hFE	100		
IC = -1.0 IIIA, VCE = -0.5 V	2N2944A 2N2945A		70		
	2N2946A		50		
Forward-Current Transfer Ratio (inverted connection)			- 50		
1		hEE(inv)	50		
$I_E = -200 \mu A, V_{EC} = -0.5 V$	2N2944A 2N2945A	hFE(inv)	50		
	2N2946A		30 20		
Emitter Collector Offeet Voltage	ZINZ340A		20		
Emitter-Collector Offset Voltage	01100444	\/E0(ata)		-0.3	mV
$I_B = -200 \mu A, I_E = 0$	2N2944A	VEC(ofs)		-0.5 -0.5	111.0
	2N2945A			-0.5	
	2N2946A			-0.6	
$I_B = -1.0 \text{ mA}, I_E = 0$	2N2944A			-1.0	
	2N2945A			-2.0	
	2N2946A			-2.0 -1.0	
$I_B = -2.0 \text{ mA}, I_E = 0$	2N2944A			-1.6	
	2N2945A			-1.6	
	2N2946A			-2.5	
DYNAMIC CHARACTERISTICS:					
Emitter-Collector On-State Resistance					
$I_B = -100 \mu A$, $I_E = 0$, $I_e = 100 \mu A$ ac (rms)	2N2944A	r _{ec} (on)		10	
f = 1.0 kHz	2N2945A			12	
	2N2946A			14	Ω
$I_B = -1.0 \text{ mA}, I_E = 0, I_e = 100 \mu A \text{ ac (rms)}$	2N2944A			4.0	
f =1.0 kHz	2N2945A			6.0	
	2N2946A			8.0	
Magnitude of Small-Signal Forward					
Current Transfer Ratio	2N2944A	h _{fe}	15	55	
$I_C = -1.0 \text{ mA}, V_{CE} = -6.0 \text{V}, f = 1.0 \text{ MHz}$	2N2945A		10	55	
, 32 ,	2N2946A		5.0	55	
Output Capacitance		_			_
$V_{CB} = -6.0 \text{ V}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$		C _{obo}		10	pF
Input Capacitance					
1 .		C _{ibo}		6.0	pF
$V_{EB} = -6.0 \text{ V}, I_C = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$					

⁽¹⁾ Pulse Test: Pulse Width = 300 s, duty cycle 2.0%.



GRAPHS

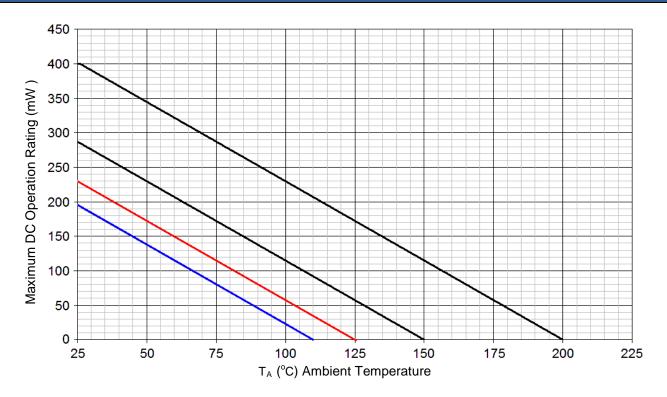
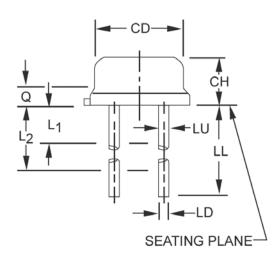
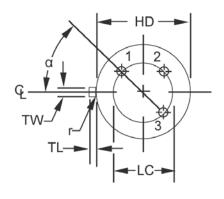


FIGURE 1 – Temperature-Power Derating Curve



PACKAGE DIMENSIONS





	Dimensions				
Ltr.	Inches Millimeters		Notes		
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
CH	.065	.085	1.65	2.16	
HD	.209	.230	5.31	5.84	
LC	.10	0 TP	2.54 TP		5
LD	.016	.021	0.41	0.53	
LL	.500	1.750	12.70	44.45	6
LU	.016	.019	0.41	0.48	6
L1		.050		1.27	6
L2	.250		6.35		6
Q		.040		1.02	3
TL	.028	.048	0.71	1.22	8
TW	.036	.046	0.91	1.17	4
r		.010		0.25	9
α	45° TP		45° TP		5

NOTES:

- 1. Dimensions are in inches.
- Millimeters are given for general information only.
 Symbol TL is measured from HD maximum.
- 4. Details of outline in this zone are optional.
- 5. Leads at gauge plane .054 inch (1.37 mm) +.001 inch (0.03 mm) -.000 inch (0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of TP relative to tab. Device may be measured by direct methods or by gauge.
- 6. Symbol LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum.
- 7. Lead number three is electrically connected to case.
- 8. Beyond r maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
- 9. Symbol r applied to both inside corners of tab.
- 10. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
- 11. Lead 1 is emitter, lead 2 is base, and lead 3 is collector.